

## AMENDMENTS

### In the Claims:

Please amend claim 1 as follows:

1. (Amended) A nitride compound semiconductor light emitting device comprising:  
a GaN substrate having a crystal orientation which is tilted away from a  $\langle 0001 \rangle$  direction by an angle which equal to or greater than about  $0.05^\circ$  and which is equal to or less than about  $2^\circ$ , and  
a semiconductor multilayer structure formed on the GaN substrate,  
wherein the semiconductor multilayer structure it includes:  
an acceptor doping layer containing a nitride compound semiconductor comprising  $\text{Ga}_x\text{In}_y\text{Al}_{(1-(x+y))}\text{N}$  (where  $0 \leq y \leq 1$ ,  $0 \leq x \leq 1$ ,  $0 \leq x+y \leq 1$ , and  
an active layer including a light emitting region, and  
wherein said active layer is formed evenly.

Please add claim 12 as follows:

12. (New ) A nitride compound semiconductor light emitting device comprising:  
a GaN substrate having a crystal orientation which is tilted away from a  $\langle 0001 \rangle$  direction by an angle which is equal to or greater than about  $0.05^\circ$  and which is equal to or less than about  $2^\circ$ , and  
a semiconductor multilayer structure formed on the GaN substrate,  
wherein the semiconductor multilayer structure includes:

an acceptor doping layer containing a nitride compound semiconductor comprising  $\text{Ga}_x\text{In}_y\text{Al}_{(1-(x+y))}\text{N}$  (where  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  $0 \leq x+y \leq 1$ , and an active layer including a light emitting region, and wherein said acceptor doping layer is formed evenly.